

Dongxia Shi

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112
papers

7,289
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39
h-index

85
g-index

118
ext. papers

8,561
ext. citations

9.2
avg, IF

5.54
L-index

#	Paper	IF	Citations
112	Epitaxial growth of single-domain graphene on hexagonal boron nitride. <i>Nature Materials</i> , 2013 , 12, 792-797	27	745
111	Super-elastic graphene ripples for flexible strain sensors. <i>ACS Nano</i> , 2011 , 5, 3645-50	16.7	542
110	Highly Ordered, Millimeter-Scale, Continuous, Single-Crystalline Graphene Monolayer Formed on Ru (0001). <i>Advanced Materials</i> , 2009 , 21, 2777-2780	24	351
109	Wafer-Scale Growth and Transfer of Highly-Oriented Monolayer MoS Continuous Films. <i>ACS Nano</i> , 2017 , 11, 12001-12007	16.7	264
108	Ultra-sensitive strain sensors based on piezoresistive nanographene films. <i>Applied Physics Letters</i> , 2012 , 101, 063112	3.4	244
107	Oxygen-Assisted Chemical Vapor Deposition Growth of Large Single-Crystal and High-Quality Monolayer MoS ₂ . <i>Journal of the American Chemical Society</i> , 2015 , 137, 15632-5	16.4	243
106	Formation of Silver Nanoparticles and Self-Assembled Two-Dimensional Ordered Superlattice. <i>Langmuir</i> , 2001 , 17, 1571-1575	4	238
105	Argon Plasma Induced Phase Transition in Monolayer MoS. <i>Journal of the American Chemical Society</i> , 2017 , 139, 10216-10219	16.4	234
104	Scalable growth of high-quality polycrystalline MoS ₂ monolayers on SiO ₂ with tunable grain sizes. <i>ACS Nano</i> , 2014 , 8, 6024-30	16.7	233
103	Highly Sensitive MoS Humidity Sensors Array for Noncontact Sensation. <i>Advanced Materials</i> , 2017 , 29, 1702076	24	223
102	An anisotropic etching effect in the graphene basal plane. <i>Advanced Materials</i> , 2010 , 22, 4014-9	24	220
101	Highly ordered self-assembly with large area of Fe ₃ O ₄ nanoparticles and the magnetic properties. <i>Journal of Physical Chemistry B</i> , 2005 , 109, 23233-6	3.4	206
100	Restoration of graphene from graphene oxide by defect repair. <i>Carbon</i> , 2012 , 50, 2581-2587	10.4	205
99	Correlated states in twisted double bilayer graphene. <i>Nature Physics</i> , 2020 , 16, 520-525	16.2	194
98	Tunable piezoresistivity of nanographene films for strain sensing. <i>ACS Nano</i> , 2015 , 9, 1622-9	16.7	194
97	Catalyst-free growth of nanographene films on various substrates. <i>Nano Research</i> , 2011 , 4, 315-321	10	192
96	Observation of Strong Interlayer Coupling in MoS ₂ /WS ₂ Heterostructures. <i>Advanced Materials</i> , 2016 , 28, 1950-6	24	172

95	Boundary activated hydrogen evolution reaction on monolayer MoS. <i>Nature Communications</i> , 2019 , 10, 1348	17.4	168
94	Patterning graphene with zigzag edges by self-aligned anisotropic etching. <i>Advanced Materials</i> , 2011 , 23, 3061-5	24	150
93	Graphene-Contacted Ultrashort Channel Monolayer MoS Transistors. <i>Advanced Materials</i> , 2017 , 29, 1702522	24	144
92	Current-driven magnetization switching in a van der Waals ferromagnet FeGeTe. <i>Science Advances</i> , 2019 , 5, eaaw8904	14.3	119
91	Thermally Induced Graphene Rotation on Hexagonal Boron Nitride. <i>Physical Review Letters</i> , 2016 , 116, 126101	7.4	103
90	Multilevel resistive switching in planar graphene/SiO ₂ nanogap structures. <i>ACS Nano</i> , 2012 , 6, 4214-21	16.7	95
89	Large-scale flexible and transparent electronics based on monolayer molybdenum disulfide field-effect transistors. <i>Nature Electronics</i> , 2020 , 3, 711-717	28.4	90
88	Growth, characterization, and properties of nanographene. <i>Small</i> , 2012 , 8, 1429-35	11	77
87	Precisely Aligned Monolayer MoS Epitaxially Grown on h-BN basal Plane. <i>Small</i> , 2017 , 13, 1603005	11	73
86	Reversible, erasable, and rewritable nanorecording on an H ₂ rotaxane thin film. <i>Journal of the American Chemical Society</i> , 2007 , 129, 2204-5	16.4	70
85	Wafer-Scale Highly Oriented Monolayer MoS with Large Domain Sizes. <i>Nano Letters</i> , 2020 , 20, 7193-7199	11.5	69
84	Twist angle-dependent conductivities across MoS/graphene heterojunctions. <i>Nature Communications</i> , 2018 , 9, 4068	17.4	59
83	Tunable electroluminescence in planar graphene/SiO ₂ memristors. <i>Advanced Materials</i> , 2013 , 25, 5593-8	8.1	56
82	Gate tunable MoS ₂ Black phosphorus heterojunction devices. <i>2D Materials</i> , 2015 , 2, 034009	5.9	55
81	Precise control of the interlayer twist angle in large scale MoS homostructures. <i>Nature Communications</i> , 2020 , 11, 2153	17.4	55
80	Gate tunable WSe ₂ -BP van der Waals heterojunction devices. <i>Nanoscale</i> , 2016 , 8, 3254-8	7.7	50
79	From Type-II Triply Degenerate Nodal Points and Three-Band Nodal Rings to Type-II Dirac Points in Centrosymmetric Zirconium Oxide. <i>Journal of Physical Chemistry Letters</i> , 2017 , 8, 5792-5797	6.4	49
78	Observation of Raman g-peak split for graphene nanoribbons with hydrogen-terminated zigzag edges. <i>Nano Letters</i> , 2011 , 11, 4083-8	11.5	47

77	Studies of graphene-based nanoelectromechanical switches. <i>Nano Research</i> , 2012 , 5, 82-87	10	46
76	Isolated nanographene crystals for nano-floating gate in charge trapping memory. <i>Scientific Reports</i> , 2013 , 3, 2126	4.9	46
75	Artificial Synapse Based on van der Waals Heterostructures with Tunable Synaptic Functions for Neuromorphic Computing. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 11945-11954	9.5	43
74	A general route towards defect and pore engineering in graphene. <i>Small</i> , 2014 , 10, 2280-4	11	42
73	Graphene edge lithography. <i>Nano Letters</i> , 2012 , 12, 4642-6	11.5	39
72	Rolling Up a Monolayer MoS ₂ Sheet. <i>Small</i> , 2016 , 12, 3770-4	11	39
71	Two-step growth of graphene with separate controlling nucleation and edge growth directly on SiO ₂ substrates. <i>Carbon</i> , 2014 , 72, 387-392	10.4	38
70	Integrated Flexible and High-Quality Thin Film Transistors Based on Monolayer MoS ₂ . <i>Advanced Electronic Materials</i> , 2016 , 2, 1500379	6.4	37
69	Lattice Dynamics, Phonon Chirality, and SpinPhonon Coupling in 2D Itinerant Ferromagnet Fe ₃ GeTe ₂ . <i>Advanced Functional Materials</i> , 2019 , 29, 1904734	15.6	33
68	Identification of structural defects in graphitic materials by gas-phase anisotropic etching. <i>Nanoscale</i> , 2012 , 4, 2005-9	7.7	33
67	Modulating PL and electronic structures of MoS ₂ /graphene heterostructures via interlayer twisting angle. <i>Applied Physics Letters</i> , 2017 , 111, 263106	3.4	31
66	Vapour-phase graphene epitaxy at low temperatures. <i>Nano Research</i> , 2012 , 5, 258-264	10	30
65	Patterned Peeling 2D MoS ₂ off the Substrate. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 16546-50	9.5	28
64	A route toward digital manipulation of water nanodroplets on surfaces. <i>ACS Nano</i> , 2014 , 8, 3955-60	16.7	28
63	Hofstadter Butterfly and Many-Body Effects in Epitaxial Graphene Superlattice. <i>Nano Letters</i> , 2016 , 16, 2387-92	11.5	25
62	New Floating Gate Memory with Excellent Retention Characteristics. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800726	6.4	25
61	Epitaxial fabrication of two-dimensional NiSe ₂ on Ni(111) substrate. <i>Applied Physics Letters</i> , 2017 , 111, 113107	3.4	21
60	In Situ Oxygen Doping of Monolayer MoS for Novel Electronics. <i>Small</i> , 2020 , 16, e2004276	11	21

59	Strongly enhanced exciton-phonon coupling in two-dimensional WSe ₂ . <i>Physical Review B</i> , 2018 , 97,	3.3	21
58	Ultra-low friction and edge-pinning effect in large-lattice-mismatch van der Waals heterostructures. <i>Nature Materials</i> , 2021 ,	27	21
57	Robust spin-valley polarization in commensurate MoS ₂ /graphene heterostructures. <i>Physical Review B</i> , 2018 , 97,	3.3	20
56	A Reliable All-2D Materials Artificial Synapse for High Energy-Efficient Neuromorphic Computing. <i>Advanced Functional Materials</i> , 2021 , 31, 2011083	15.6	20
55	Magnetotransport Properties of Graphene Nanoribbons with Zigzag Edges. <i>Physical Review Letters</i> , 2018 , 120, 216601	7.4	19
54	Temperature-driven evolution of critical points, interlayer coupling, and layer polarization in bilayer MoS ₂ . <i>Physical Review B</i> , 2018 , 97,	3.3	18
53	Competitive Growth and Etching of Epitaxial Graphene. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 26929-26931	3.8	18
52	Investigation on interface related charge trap and loss characteristics of high-k based trapping structures by electrostatic force microscopy. <i>Applied Physics Letters</i> , 2011 , 99, 223504	3.4	18
51	Synthesis, characterization and self-assemblies of magnetite nanoparticles. <i>Surface and Interface Analysis</i> , 2006 , 38, 1063-1067	1.5	18
50	Bandgap broadening at grain boundaries in single-layer MoS ₂ . <i>Nano Research</i> , 2018 , 11, 6102-6109	10	17
49	Graphene nanoribbons epitaxy on boron nitride. <i>Applied Physics Letters</i> , 2016 , 108, 113103	3.4	17
48	Patterning monolayer graphene with zigzag edges on hexagonal boron nitride by anisotropic etching. <i>Applied Physics Letters</i> , 2016 , 109, 053101	3.4	17
47	The Effect of Twin Grain Boundary Tuned by Temperature on the Electrical Transport Properties of Monolayer MoS ₂ . <i>Crystals</i> , 2016 , 6, 115	2.3	15
46	Atomic Layer Deposition of Al ₂ O ₃ Directly on 2D Materials for High-Performance Electronics. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1802055	4.6	14
45	Fabrication of high-quality all-graphene devices with low contact resistances. <i>Nano Research</i> , 2014 , 7, 1449-1456	10	14
44	Manipulation and four-probe analysis of nanowires in UHV by application of four tunneling microscope tips: a new method for the investigation of electrical transport through nanowires. <i>Surface and Interface Analysis</i> , 2006 , 38, 1096-1102	1.5	11
43	Two-dimensional self-organization of 1-nonanethiol-capped gold nanoparticles. <i>Science Bulletin</i> , 2001 , 46, 996-998		11
42	Strongly distinct electrical response between circular and valley polarization in bilayer transition metal dichalcogenides. <i>Physical Review B</i> , 2019 , 99,	3.3	10

41	Vertical Integration of 2D Building Blocks for All-2D Electronics. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000550	6.4	10
40	Electronic structure-dependent magneto-optical Raman effect in atomically thin WS ₂ . <i>2D Materials</i> , 2018 , 5, 035028	5.9	9
39	Alternating the Crystalline Structural Transition of Coronene Molecular Overlayers on Ag(110) through Temperature Increase. <i>Journal of Physical Chemistry C</i> , 2009 , 113, 17643-17647	3.8	8
38	Synthesis and characterization of C ₃ N ₄ hard films. <i>Science in China Series A: Mathematics</i> , 2000 , 43, 185-198		8
37	Robust circular polarization of indirect Q-K transitions in bilayer 3RWS ₂ . <i>Physical Review B</i> , 2019 , 100,	3.3	7
36	A facile and efficient dry transfer technique for two-dimensional Van derWaals heterostructure. <i>Chinese Physics B</i> , 2017 , 26, 087306	1.2	7
35	A review of nanographene: growth and applications. <i>Modern Physics Letters B</i> , 2014 , 28, 1430009	1.6	7
34	Giant Valley Coherence at Room Temperature in 3R WS with Broken Inversion Symmetry. <i>Research</i> , 2019 , 2019, 6494565	7.8	7
33	Strong and tunable interlayer coupling of infrared-active phonons to excitons in van der Waals heterostructures. <i>Physical Review B</i> , 2019 , 99,	3.3	6
32	Processing of an atomically smooth Ge(001) surface on a large scale. <i>Nanotechnology</i> , 2006 , 17, 2396-2398	3.4	6
31	Wafer-Scale Oxygen-Doped MoS Monolayer.. <i>Small Methods</i> , 2021 , 5, e2100091	12.8	6
30	Emergence of Chern Insulating States in Non-Magic Angle Twisted Bilayer Graphene. <i>Chinese Physics Letters</i> , 2021 , 38, 047301	1.8	6
29	Gate-tunable large-scale flexible monolayer MoS ₂ devices for photodetectors and optoelectronic synapses. <i>Nano Research</i> , 1	10	6
28	Structural Transition and Thermal Stability of a Coronene Molecular Monolayer on Cu(110). <i>Journal of Physical Chemistry C</i> , 2010 , 114, 11180-11184	3.8	5
27	A new model of phycobilisome in <i>Spirulina platensis</i> . <i>Science in China Series C: Life Sciences</i> , 1999 , 42, 74-9		5
26	Band evolution of two-dimensional transition metal dichalcogenides under electric fields. <i>Applied Physics Letters</i> , 2019 , 115, 083104	3.4	4
25	Nanographene charge trapping memory with a large memory window. <i>Nanotechnology</i> , 2015 , 26, 455704	3.4	4
24	Defect-enhanced coupling between graphene and SiO ₂ substrate. <i>Applied Physics Letters</i> , 2014 , 105, 063113	3.4	4

23	Identifying multiple configurations of complex molecules on metal surfaces. <i>Small</i> , 2012 , 8, 796-806, 795	11	4
22	Scanning tunneling microscope study of polyacrylonitrile-based carbon fibers. <i>Journal of Materials Research</i> , 1997 , 12, 2543-2547	2.5	4
21	Scratching lithography for wafer-scale MoS ₂ monolayers. <i>2D Materials</i> , 2020 , 7, 045028	5.9	4
20	Nonvolatile Memory: New Floating Gate Memory with Excellent Retention Characteristics (Adv. Electron. Mater. 4/2019). <i>Advanced Electronic Materials</i> , 2019 , 5, 1970018	6.4	3
19	Interlayer exciton complexes in bilayer MoS ₂ . <i>Physical Review B</i> , 2022 , 105,	3.3	3
18	Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Annealing in Air. <i>Acta Chimica Sinica</i> , 2015 , 73, 954	3.3	3
17	Observation of logarithmic Kohn anomaly in monolayer graphene. <i>Physical Review B</i> , 2020 , 102,	3.3	3
16	Pressure-mediated contact quality improvement between monolayer MoS ₂ and graphite. <i>Chinese Physics B</i> , 2019 , 28, 017301	1.2	2
15	Spatially indirect intervalley excitons in bilayer WSe ₂ . <i>Physical Review B</i> , 2022 , 105,	3.3	2
14	A review of experimental advances in twisted graphene moiré superlattice. <i>Chinese Physics B</i> , 2020 , 29, 128104	1.2	2
13	Thermally induced band hybridization in bilayer-bilayer MoS ₂ /WS ₂ heterostructure*. <i>Chinese Physics B</i> , 2021 , 30, 057801	1.2	2
12	Atomic Layer Deposition: Atomic Layer Deposition of Al ₂ O ₃ Directly on 2D Materials for High-Performance Electronics (Adv. Mater. Interfaces 10/2019). <i>Advanced Materials Interfaces</i> , 2019 , 6, 1970065	4.6	1
11	High-order minibands and interband Landau level reconstruction in graphene moiré superlattices. <i>Physical Review B</i> , 2020 , 102,	3.3	1
10	Molecular cloisonné multicomponent organic alternating nanostructures at vicinal surfaces with tunable length scales. <i>Small</i> , 2012 , 8, 535-40	11	1
9	Surfaces: Identifying Multiple Configurations of Complex Molecules on Metal Surfaces (Small 6/2012). <i>Small</i> , 2012 , 8, 795-795	11	1
8	Study on surface and interface structures of nanocrystalline silicon by scanning tunneling microscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 1313		1
7	Artificial Synapses: A Reliable All-2D Materials Artificial Synapse for High Energy-Efficient Neuromorphic Computing (Adv. Funct. Mater. 27/2021). <i>Advanced Functional Materials</i> , 2021 , 31, 2170197	15.6	1
6	Highly Stretchable MoS ₂ -Based Transistors with Opto-Synaptic Functionalities. <i>Advanced Electronic Materials</i> , 2020 , 2200238	6.4	1

- 5 Employing defected monolayer MoS as charge storage materials. *Nanotechnology*, **2020**, 31, 235710 3-4
- 4 Reducing the contact resistance of SiNW devices by employing a heavily doped carrier injection layer. *Nanotechnology*, **2012**, 23, 305701 3-4
- 3 Inside Back Cover: Wafer-Scale Oxygen-Doped MoS₂ Monolayer (Small Methods 6/2021). *Small Methods*, **2021**, 5, 2170026 12.8
- 2 Hot-Pressed Two-Dimensional Amorphous Metals and Their Electronic Properties. *Crystals*, **2022**, 12, 616 2-3
- 1 Rail-to-Rail MoS₂ Inverters. *ACS Applied Electronic Materials*, 4